

RB751BS-40 Schottky Barrier Diode

Feature

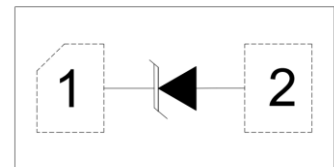
- Low Forward Voltage
- Low IR
- High Reliability

MARKING: 5

DFN1006-2L



Pin Configuration



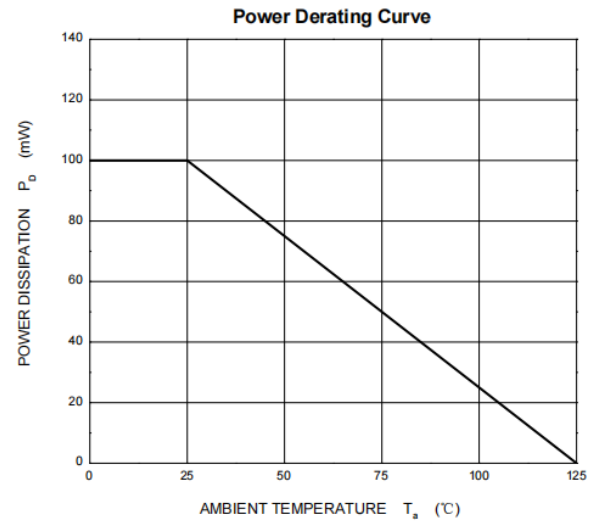
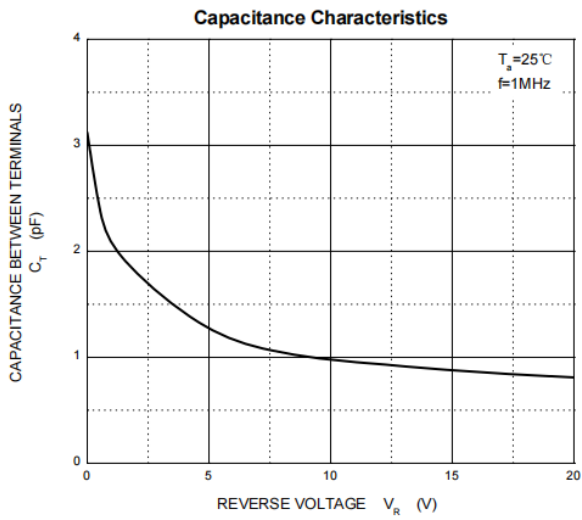
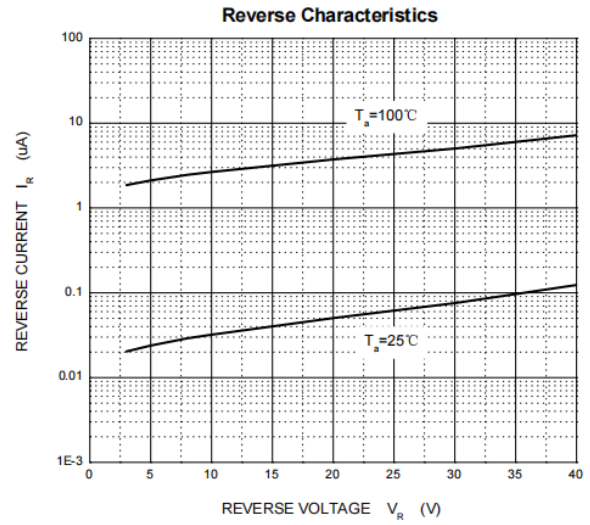
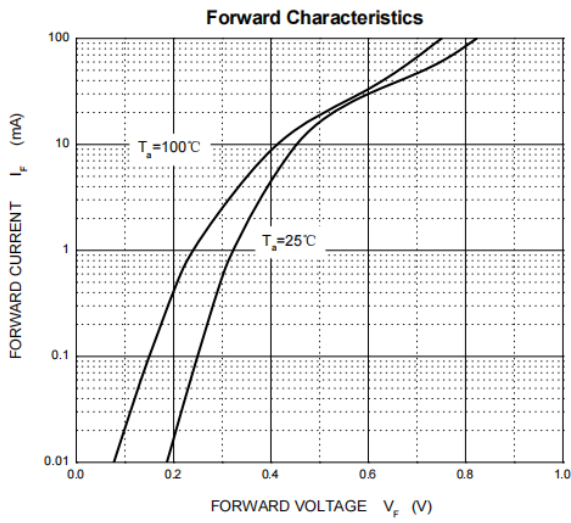
ABSOLUTE MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

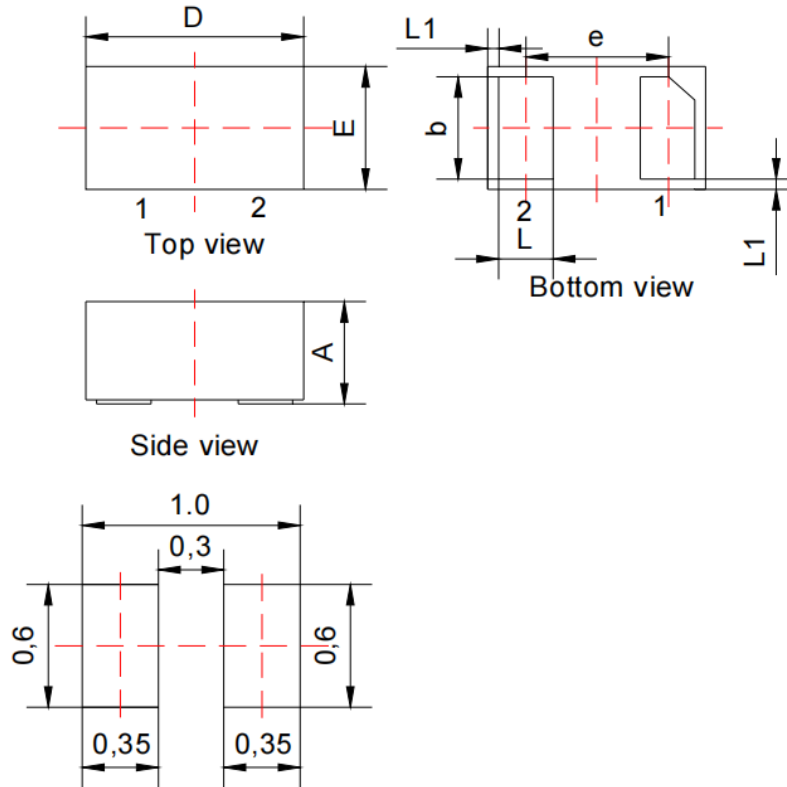
Parameter	Symbol	Value	Unit
DC reverse voltage	V _R	40	V
Mean rectifying current	I _O	30	mA
Non-repetitive Peak Forward Surge Current @ t=8.3ms	I _{FSM}	200	mA
Power Dissipation	P _D	0.1	W
Junction Temperature	T _J	-40~+125	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Reverse voltage	V _{BR}	I _R =100uA	40			V
Forward voltage	V _F	I _F =1mA			0.37	V
Reverse current	I _R	V _R =30V			0.5	μA
Capacitance between terminals	C _T	V _R =1V,f=1MHZ		2		pF

Typical Characteristics



DFN1006-2L Package Outline Dimensions


Recommended soldering footprint(mm)

Symbol	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	0.32	0.42	0.013	0.017
b	0.45	0.55	0.018	0.022
D	0.95	1.05	0.037	0.041
e	0.55	0.65	0.022	0.026
E	0.55	0.65	0.022	0.026
L	0.28	0.38	0.011	0.015
L1	0.00	0.10	0.000	0.004